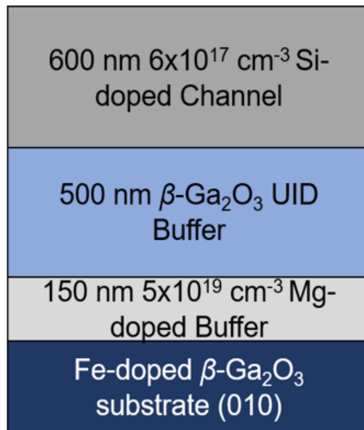


**Fig. 1**: Epitaxial structure of the device grown by MOCVD

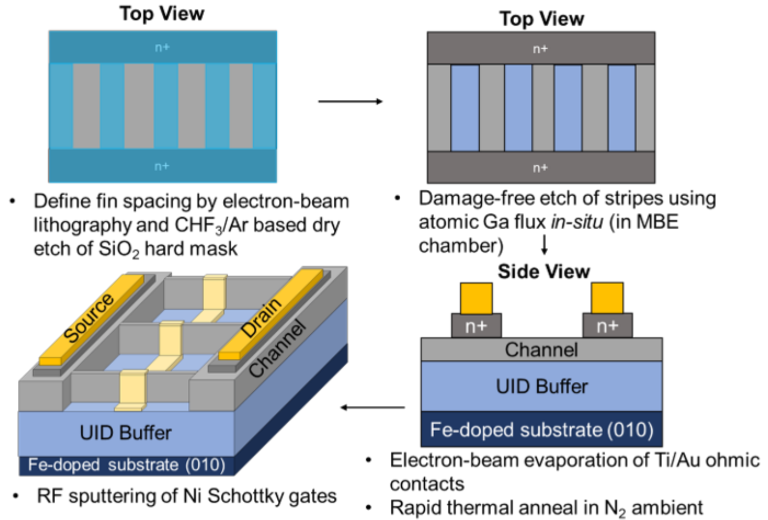


**Fig. 2**: Process flow for fabrication of FinFETs using atomic Ga flux etching

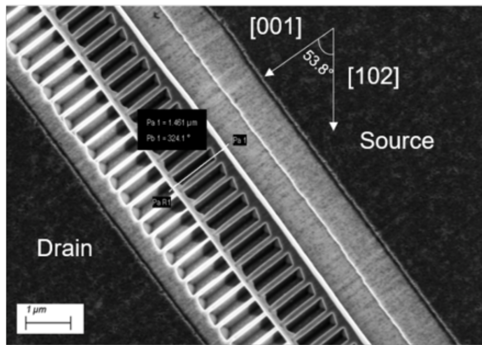


**Fig. 3**: SEM image of the fabricated $\beta$-$Ga_2O_3$ FinFETs

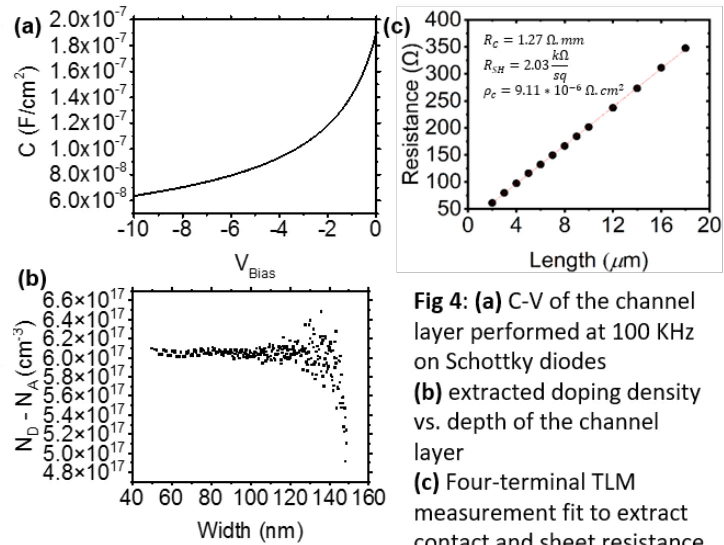


**Fig 4**: **(a)** C-V of the channel layer performed at 100 KHz on Schottky diodes
**(b)** extracted doping density vs. depth of the channel layer
**(c)** Four-terminal TLM measurement fit to extract contact and sheet resistance

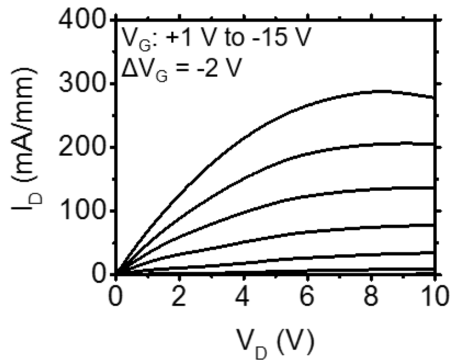


**Fig 5**: FinFET output characteristics for a gate length of 1.5 μm normalized to the fin width

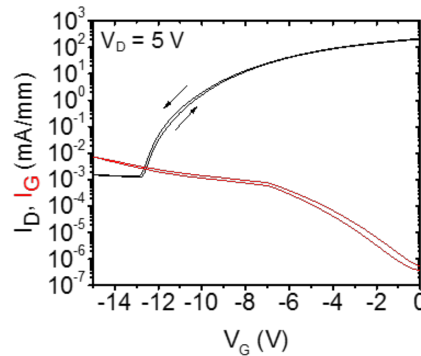


**Fig 6**: FinFET transfer characteristics (reverse/forward) and gate leakage